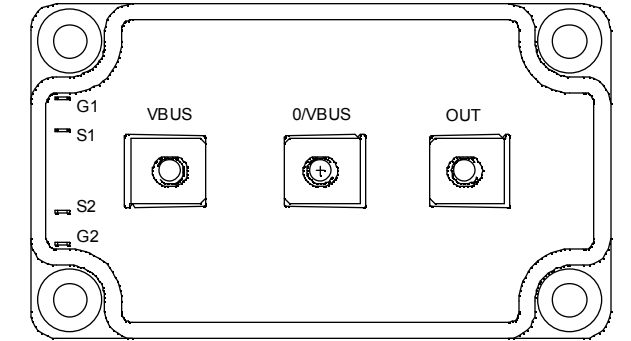
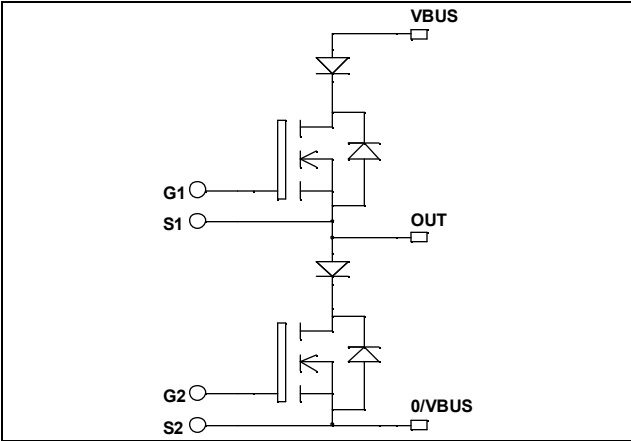


Phase leg  
with Series diodes  
MOSFET Power Module

$V_{DSS} = 1000V$   
 $R_{DSon} = 130m\Omega$  typ @  $T_j = 25^\circ C$   
 $I_D = 65A$  @  $T_c = 25^\circ C$



**Application**

- Zero Current Switching resonant mode

**Features**


- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1000	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	65
		$T_c = 80^\circ C$	49
$I_{DM}$	Pulsed Drain current	240	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	
$R_{DSon}$	Drain - Source ON Resistance	156	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	1250
$I_{AR}$	Avalanche current (repetitive and non repetitive)	24	A
$E_{AR}$	Repetitive Avalanche Energy	30	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1300	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 1000\text{V}$			600	$\mu\text{A}$
		$V_{GS} = 0\text{V}, V_{DS} = 800\text{V}$			2	$\text{mA}$
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 32.5\text{A}$		130	156	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 6\text{mA}$	3		5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			$\pm 450$	$\text{nA}$

**Dynamic Characteristics**

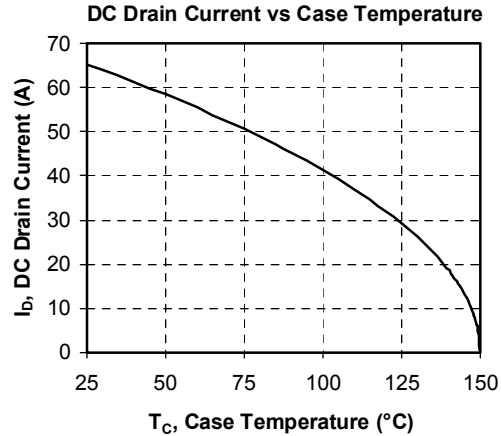
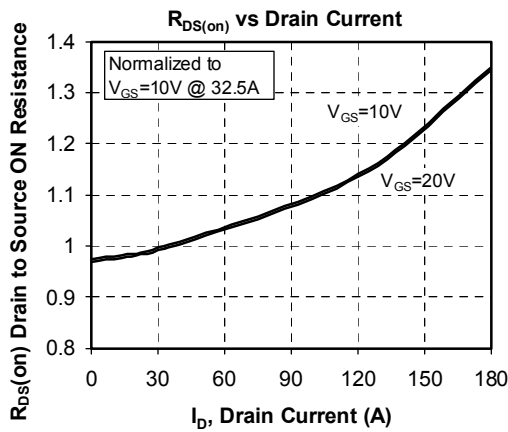
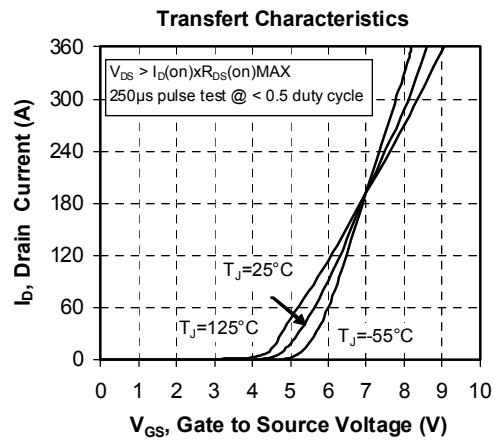
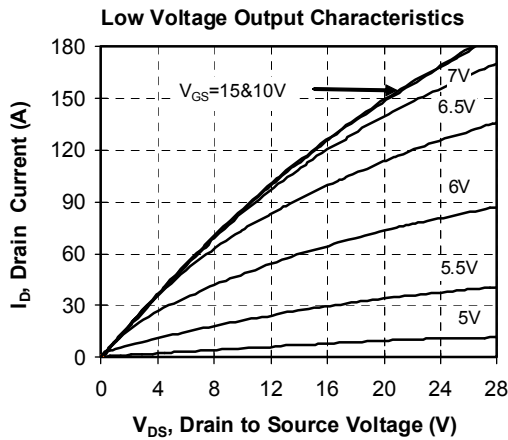
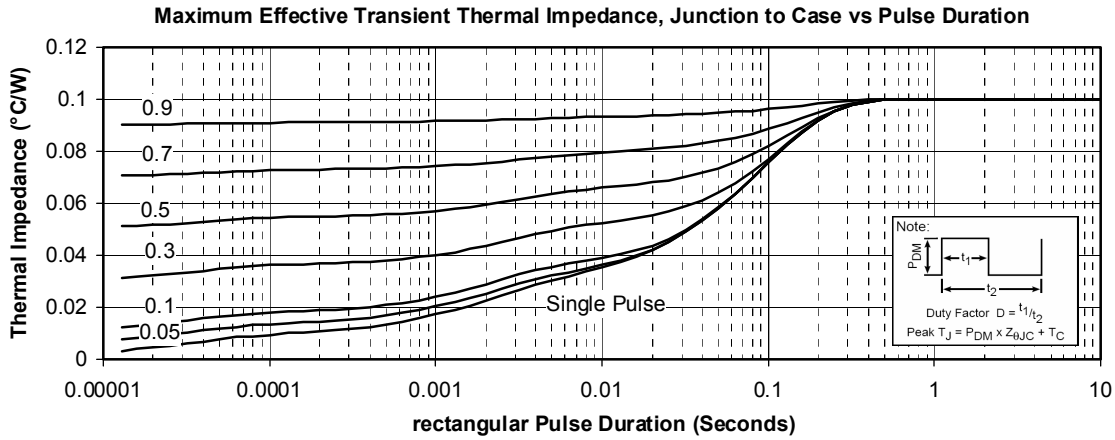
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$		15.2		$\text{nF}$
$C_{oss}$	Output Capacitance	$V_{DS} = 25\text{V}$		2.6		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.42		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$		562		$\text{nC}$
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 500\text{V}$		75		
$Q_{gd}$	Gate – Drain Charge	$I_D = 65\text{A}$		363		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b>		9		$\text{ns}$
$T_r$	Rise Time	$V_{GS} = 15\text{V}$		9		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 667\text{V}$		50		
$T_f$	Fall Time	$I_D = 65\text{A}$ $R_G = 0.5\Omega$		24		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b>		2.13		$\text{mJ}$
$E_{off}$	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 667\text{V}$ $I_D = 65\text{A}, R_G = 0.5\Omega$		0.46		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b>		4.4		$\text{mJ}$
$E_{off}$	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 667\text{V}$ $I_D = 65\text{A}, R_G = 0.5\Omega$		0.57		

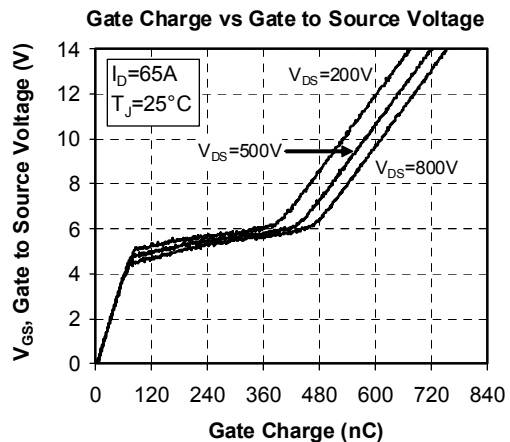
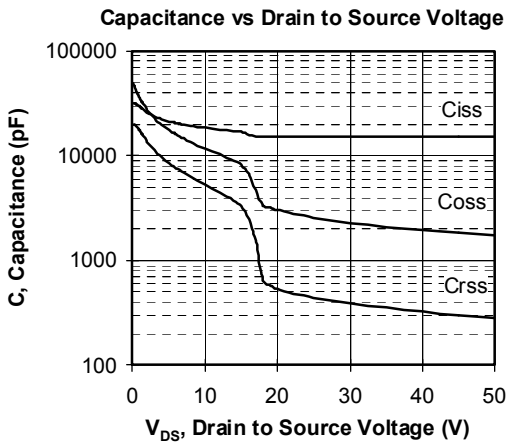
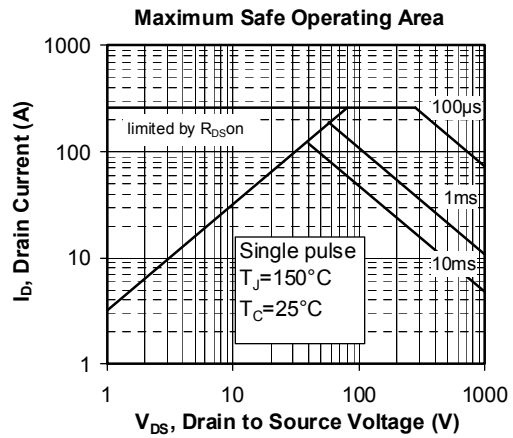
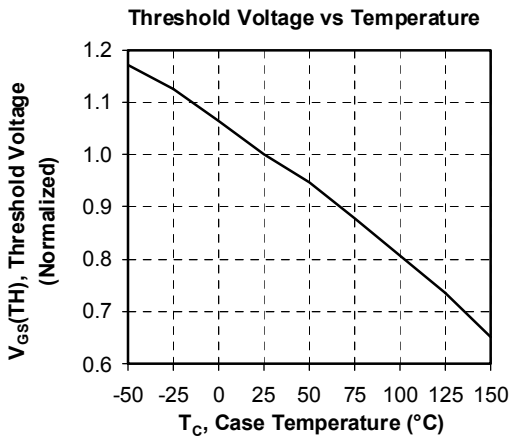
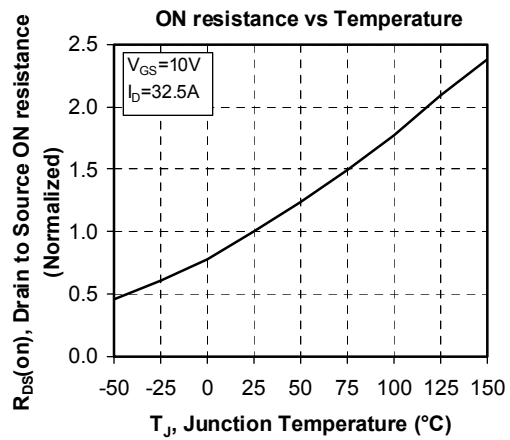
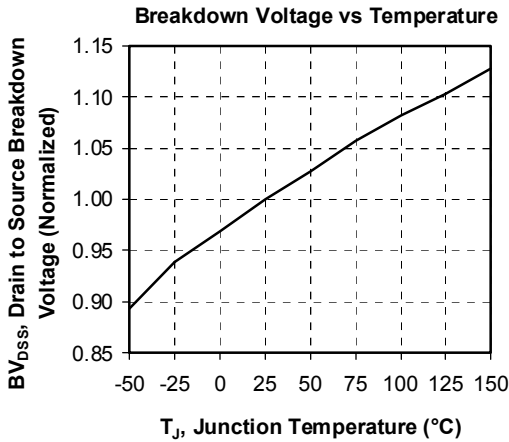
**Series diode ratings and characteristics**

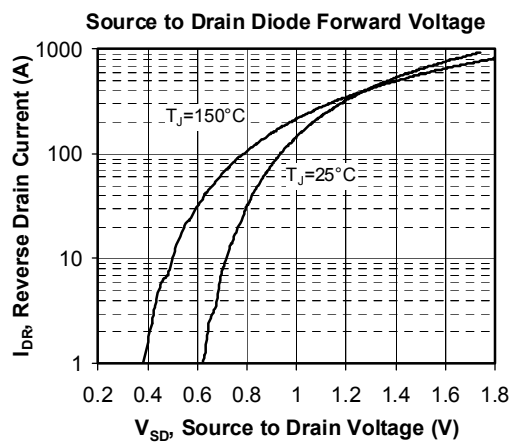
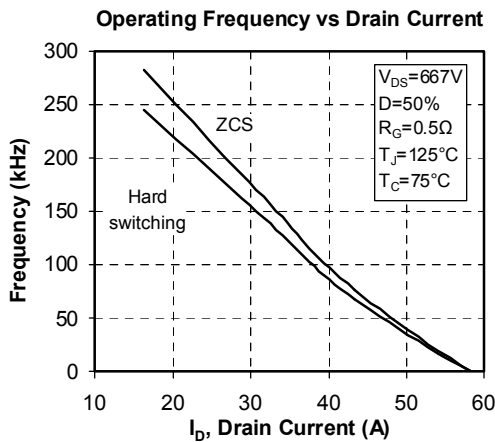
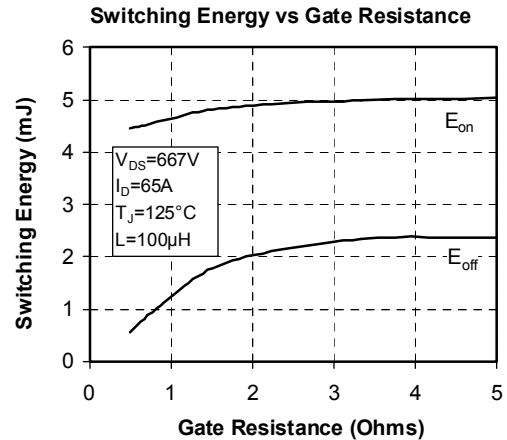
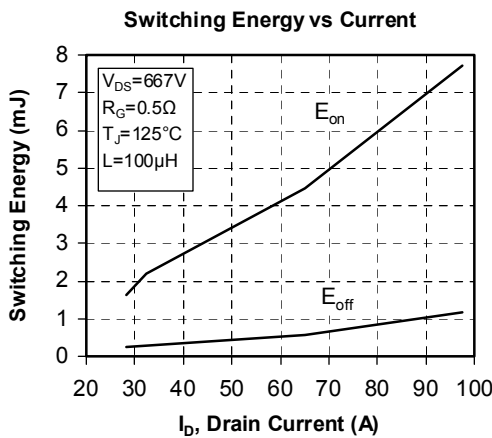
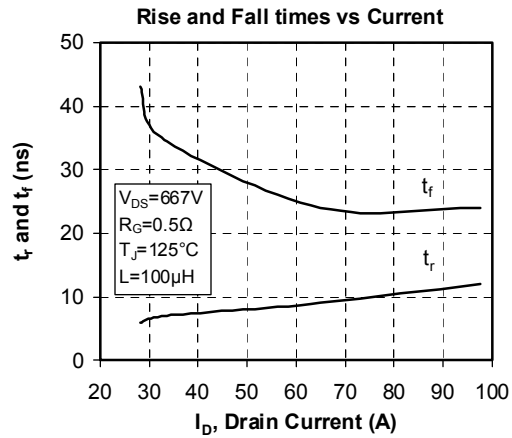
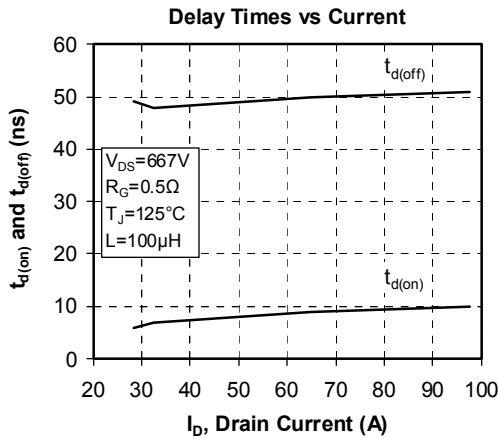
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$		150	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		600	
$I_F$	DC Forward Current	$T_c = 100^\circ\text{C}$		120		A
$V_F$	Diode Forward Voltage	$I_F = 120\text{A}$		2.5	3	V
		$I_F = 240\text{A}$		3		
		$I_F = 120\text{A}$	$T_j = 125^\circ\text{C}$	1.8		
$t_{rr}$	Reverse Recovery Time	$I_F = 120\text{A}$ $V_R = 800\text{V}$	$T_j = 25^\circ\text{C}$	265		$\text{ns}$
			$T_j = 125^\circ\text{C}$	350		
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	1120		$\text{nC}$
			$T_j = 125^\circ\text{C}$	5800		



## Typical Performance Curve







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